

## Supplementary Information

### Discovery of TaFeSb-based half-Heuslers with high thermoelectric performance

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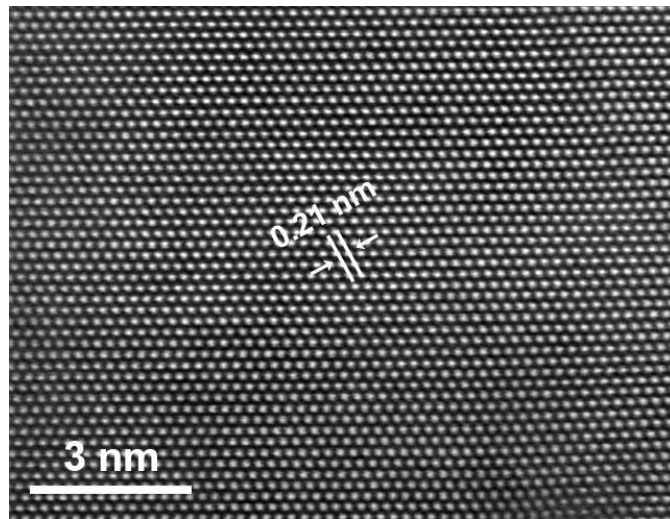
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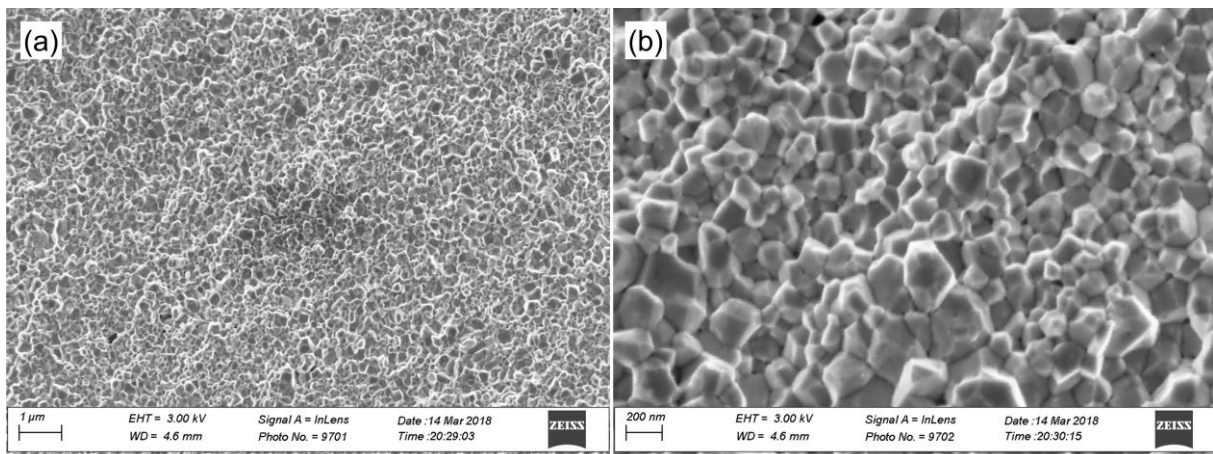
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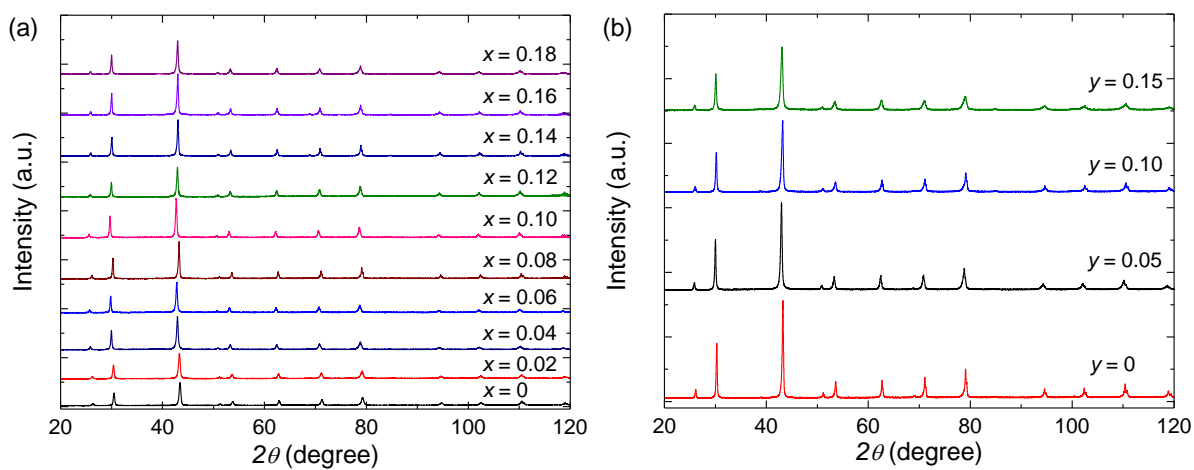
## Supplementary Figures



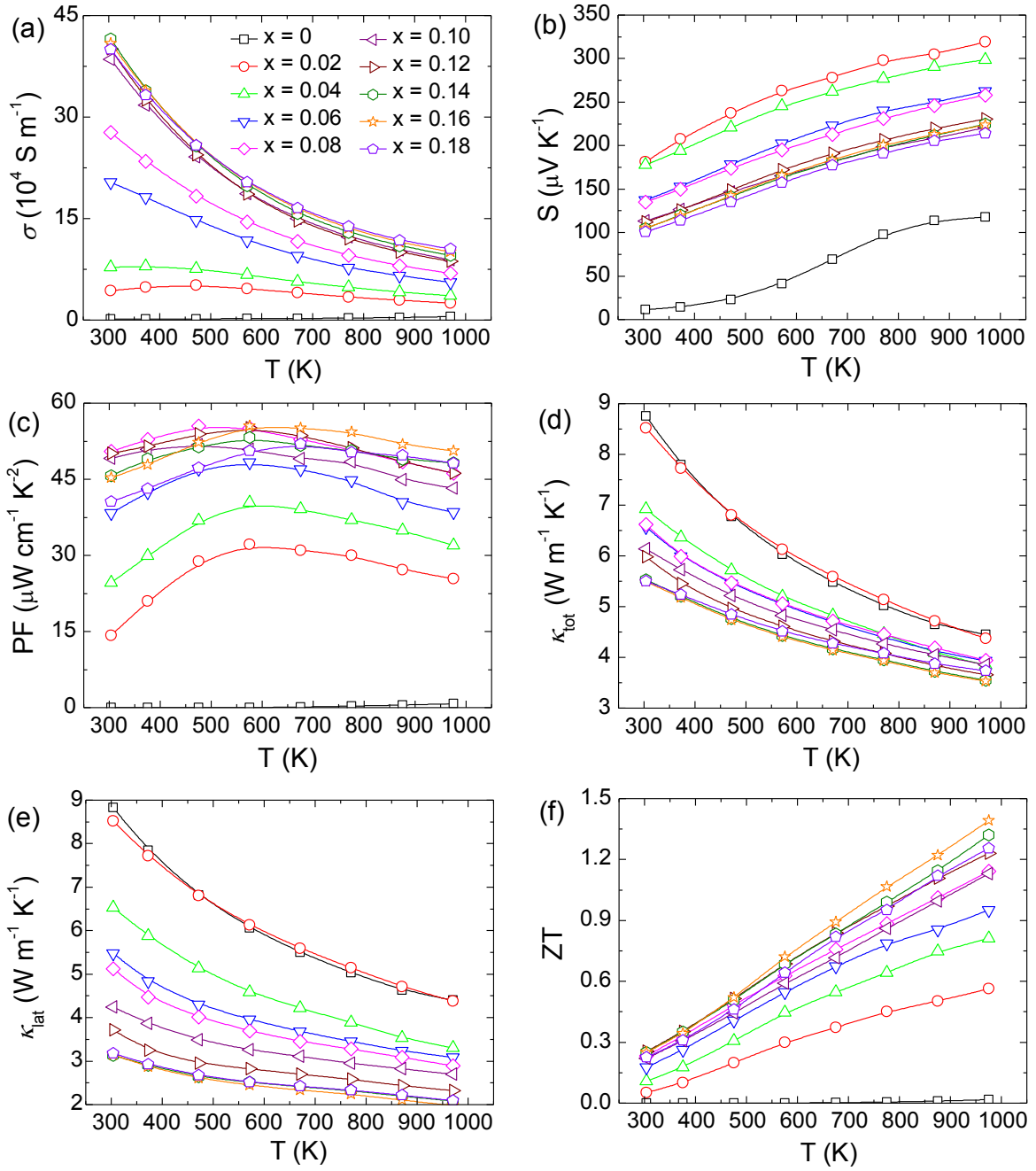
**Supplementary Figure 1.** STEM image of the prepared TaFeSb half-Heusler. The ( $2\bar{2}0$ ) plane with a spacing of  $\sim 0.21$  nm has been verified.



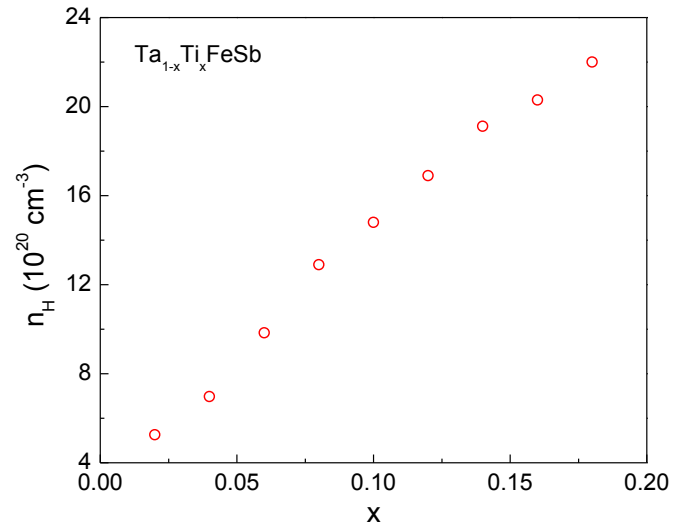
**Supplementary Figure 2.** Microstructures of the pristine TaFeSb half-Heusler. (a) and (b) Scanning electron microscopy images.



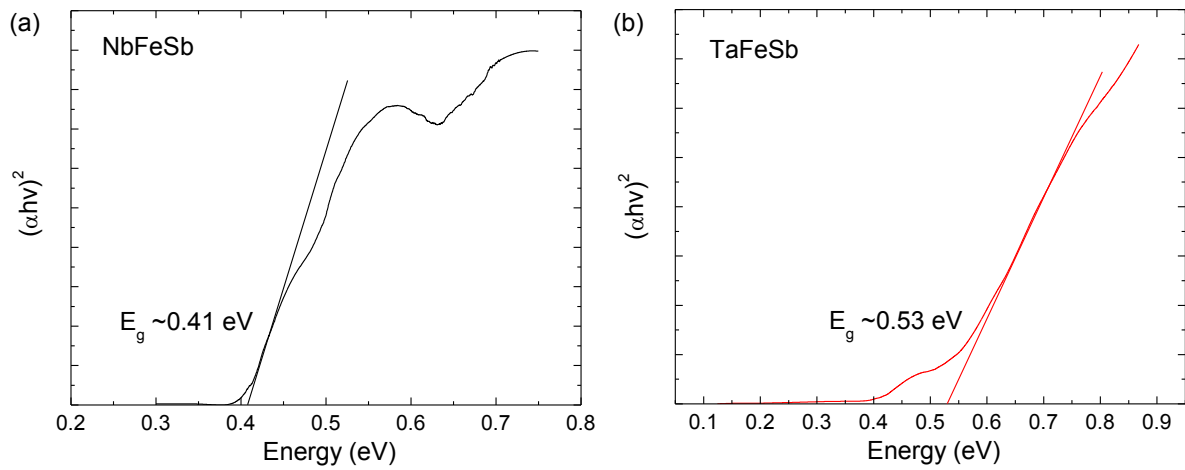
**Supplementary Figure 3. Phase composition of TaFeSb-based half-Heuslers.** XRD patterns of the prepared (a) Ta<sub>1-x</sub>Ti<sub>x</sub>FeSb ( $x = 0, 0.02, 0.04, 0.06, 0.08, 0.10, 0.12, 0.14, 0.16,$  and  $0.18$ ) and (b) Ta<sub>0.84-y</sub>V<sub>y</sub>Ti<sub>0.16</sub>FeSb ( $y = 0, 0.05, 0.10,$  and  $0.15$ ).



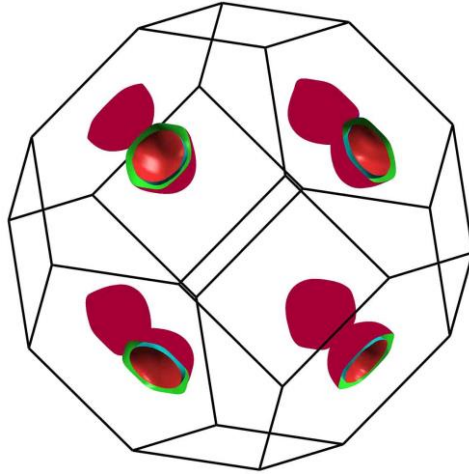
**Supplementary Figure 4. Thermoelectric properties of  $\text{Ta}_{1-x}\text{Ti}_x\text{FeSb}$  ( $x = 0, 0.02, 0.04, 0.06, 0.08, 0.10, 0.12, 0.14, 0.16, \text{ and } 0.18$ ). (a) Electrical conductivity, (b) Seebeck coefficient, (c) power factor, (d) total thermal conductivity, (e) lattice thermal conductivity, and (f)  $ZT$ .**



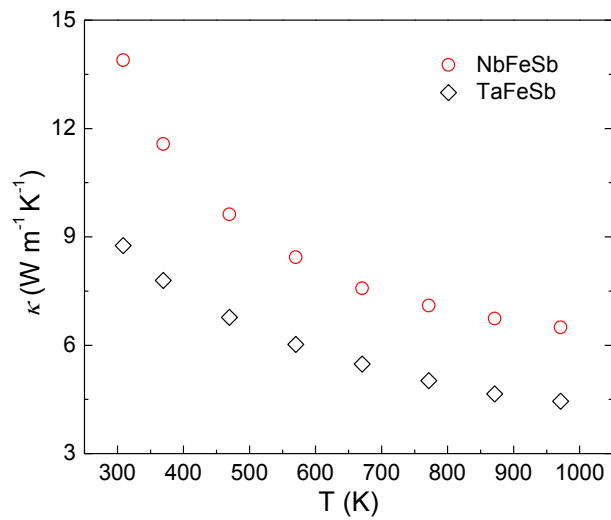
**Supplementary Figure 5. Composition-dependent room-temperature hole concentration.**



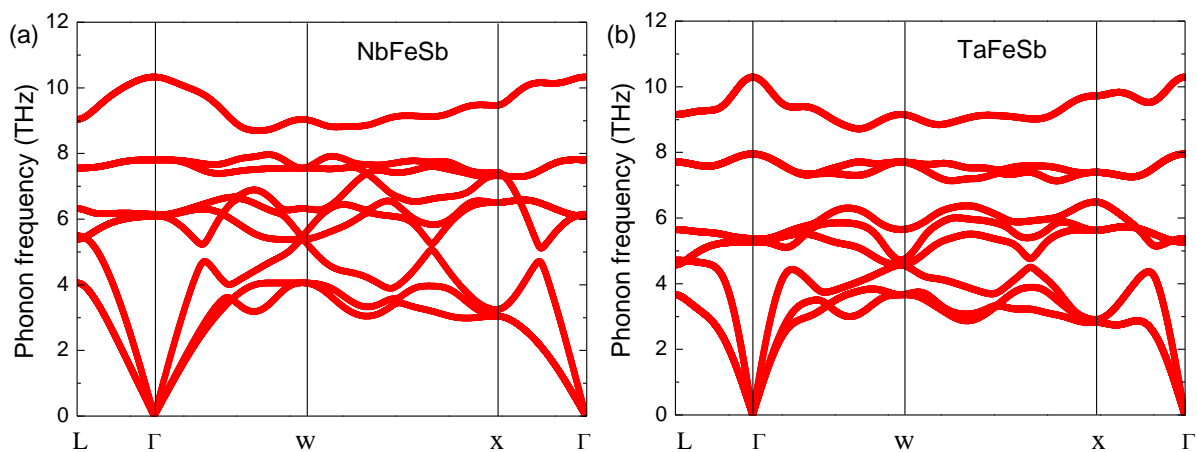
**Supplementary Figure 6. Measured bandgap of the pristine (a) NbFeSb and (b) TaFeSb.**



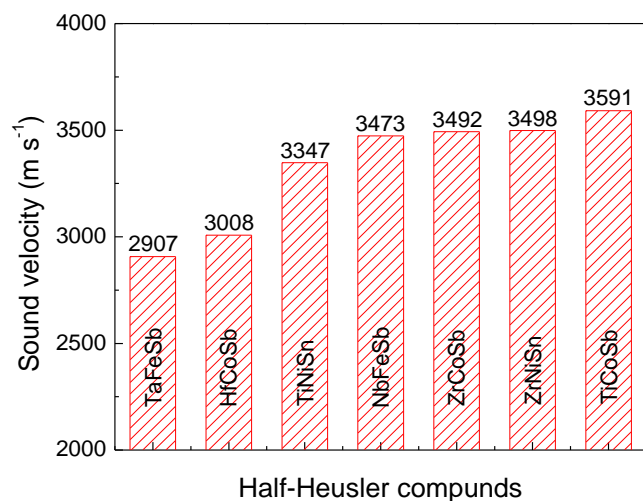
**Supplementary Figure 7. The iso-energy carrier pockets of TaFeSb at 0.1 eV below the valence band maximum.**



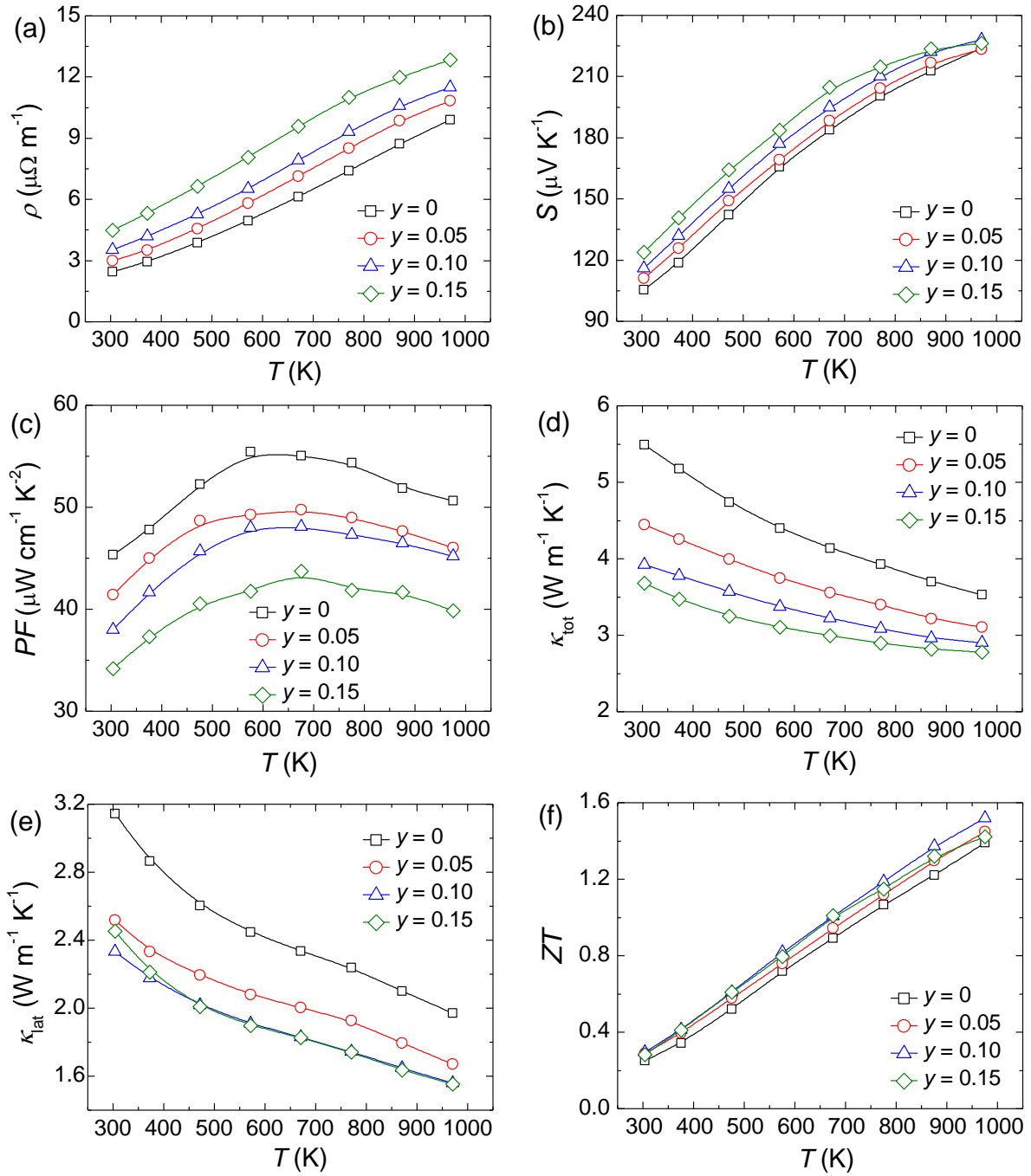
**Supplementary Figure 8. The thermal conductivity of the undoped NbFeSb and TaFeSb.** The samples are both prepared by the identical ball-milling and hot-pressing method.



**Supplementary Figure 9. Comparison of the phonon dispersion between (a) NbFeSb and (b) TaFeSb.**

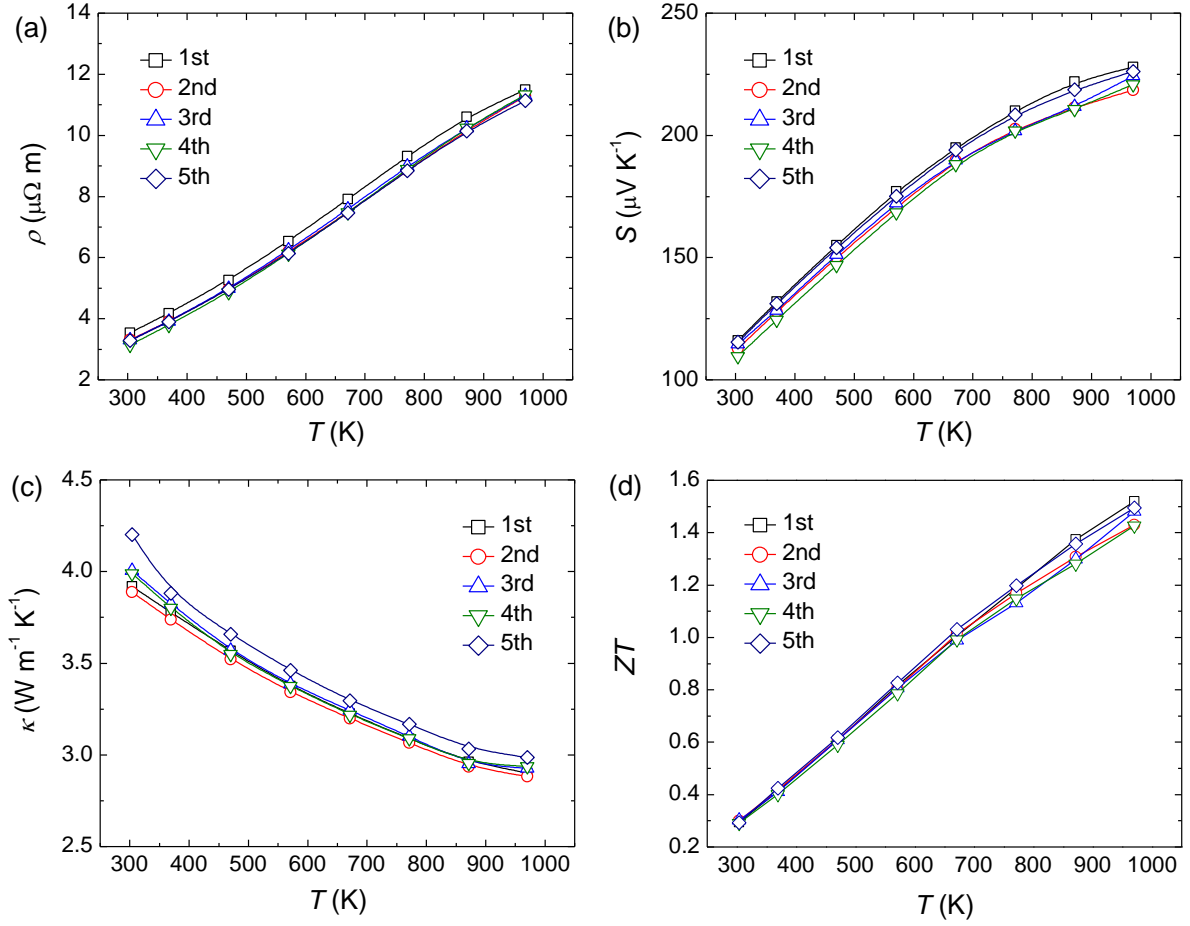


**Supplementary Figure 10. Comparison of sound velocity between several half-Heusler compounds.**

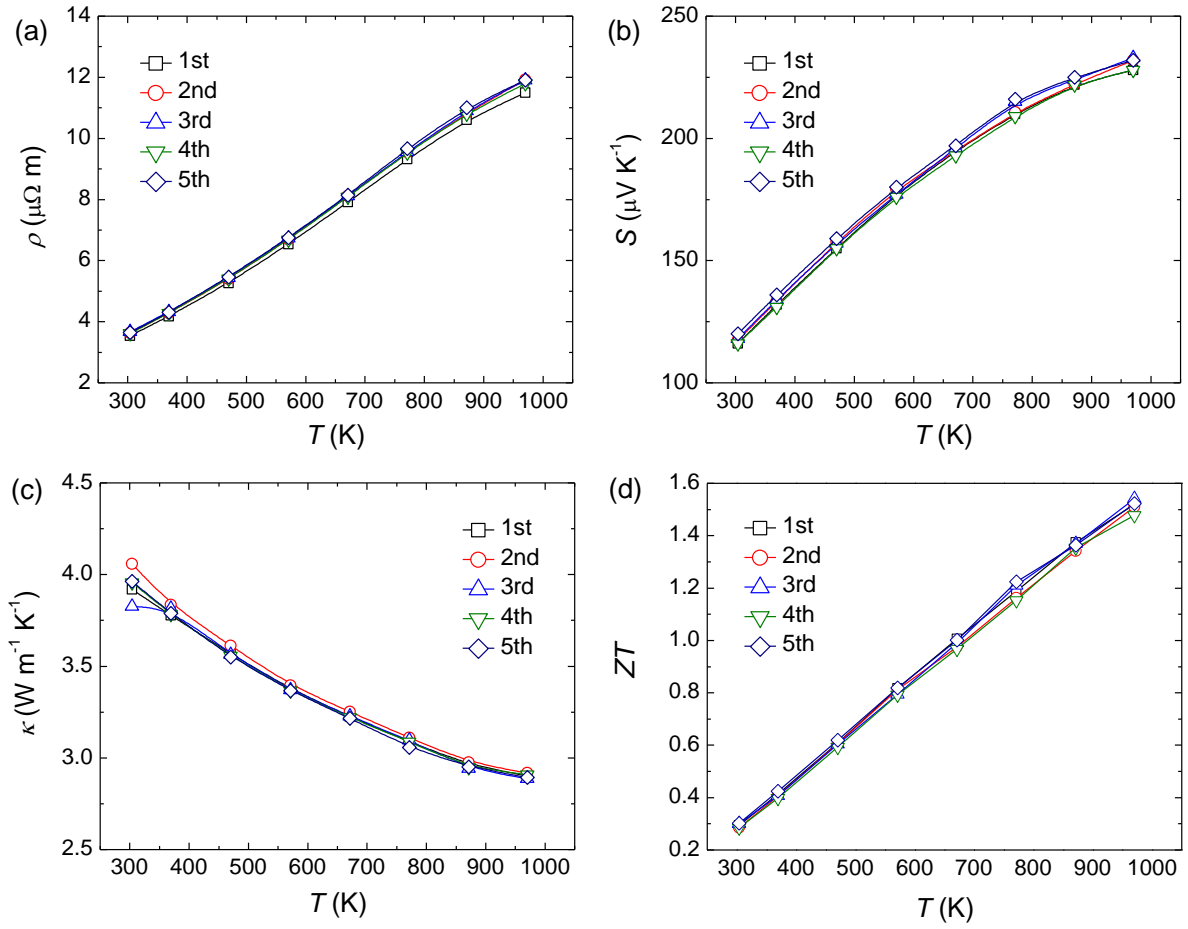


**Supplementary Figure 11. Thermoelectric properties of  $\text{Ta}_{0.84-y}\text{V}_y\text{Ti}_{0.16}\text{FeSb}$  ( $y = 0, 0.05, 0.10, \text{ and } 0.15$ ).** (a) Electrical resistivity, (b) Seebeck coefficient, (c) power factor, (d) total thermal conductivity, (e) lattice thermal conductivity, and (f)  $ZT$ .





**Supplementary Figure 12. Reproducibility of the thermoelectric properties of  $\text{Ta}_{0.74}\text{V}_{0.1}\text{Ti}_{0.16}\text{FeSb}$ .** Five different batches of  $\text{Ta}_{0.74}\text{V}_{0.1}\text{Ti}_{0.16}\text{FeSb}$  were prepared and the thermoelectric properties of the specimens were then characterized. (a) Electrical resistivity, (b) Seebeck coefficient, (c) thermal conductivity, and (d)  $ZT$ .



**Supplementary Figure 13. Thermal stability of  $\text{Ta}_{0.74}\text{V}_{0.1}\text{Ti}_{0.16}\text{FeSb}$ .** Thermoelectric properties of the same  $\text{Ta}_{0.74}\text{V}_{0.1}\text{Ti}_{0.16}\text{FeSb}$  specimen measured five times. (a) Electrical resistivity, (b) Seebeck coefficient, (c) thermal conductivity, and (d)  $ZT$ .